

## Product Summary

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
$V_{DRM} V_{RRM}$	600 / 800	V
$V_{TM}$	1.55	V

## Feature

With high ability to withstand the shock loading of large current, With high commutation performances, 3 quadrants products especially recommended for use on inductive load.

## Application

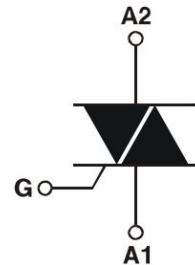
Washing machine, vacuums, massager, solid state relay, AC Motor speed regulation and so on.

## Package

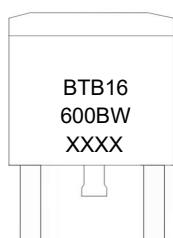


TO-263AB

## Circuit diagram



## Marking



**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value		Unit
Repetitive peak off-state voltage	V <sub>DRM</sub>	600 / 800		V
Repetitive peak reverse voltage	V <sub>RRM</sub>	600 / 800		V
RMS on-state current	I <sub>T(RMS)</sub>	16		A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I <sub>TSM</sub>	160		A
I <sup>2</sup> t value for fusing (tp=10ms)	I <sup>2</sup> t	140		A <sup>2</sup> s
Critical rate of rise of on-state current (I <sub>G</sub> =2×I <sub>GT</sub> )	dI <sub>T</sub> /dt	I - II - III	50	A/μs
Peak gate current	I <sub>GM</sub>	4		A
Average gate power dissipation	P <sub>G(AV)</sub>	1		W
Junction Temperature	T <sub>J</sub>	-40 ~ +125		°C
Storage Temperature	T <sub>STG</sub>	-40 ~ +150		°C

**Electrical characteristics (T<sub>A</sub>=25 °C, unless otherwise noted)**

Parameter	Symbol	Test Condition	Value		Unit
			CW	BW	
Gate trigger current	I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> = 33Ω T <sub>j</sub> =25°C	I - II - III	≤35	mA
Gate trigger voltage	V <sub>GT</sub>		I - II - III	≤1.3	V
Gate non-trigger voltage	V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C		≥0.2	V
latching current	I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III	≤50	mA
			II	≤60	≤80
Holding current	I <sub>H</sub>	I <sub>T</sub> =500mA		≤30	≤50
Critical-rate of rise of commutation voltage	dV <sub>D</sub> /dt	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125°C		≥500	≥1000 V/μs

**STATIC CHARACTERISTICS**

Forward "on" voltage	V <sub>TM</sub>	I <sub>TM</sub> =23A tp=380μs	≤1.55	V
Repetitive Peak Off-State Current	I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub>	T <sub>j</sub> =25°C	≤5 μA
Repetitive Peak Reverse Current	I <sub>RRM</sub>		T <sub>j</sub> =125°C	≤1 mA

**THERMAL RESISTANCES**

Thermal resistance	R <sub>th(j-c)</sub>	Junction to case(AC)	1.2	°C/W
	R <sub>th(j-a)</sub>	Junction to ambient	45	°C/W

## Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

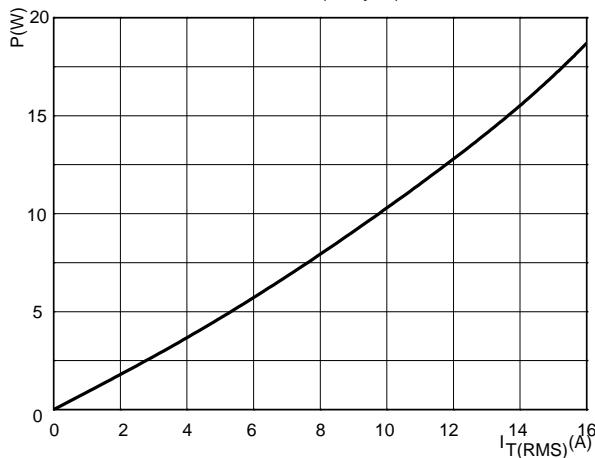


FIG.2: RMS on-state current versus case temperature (full cycle)

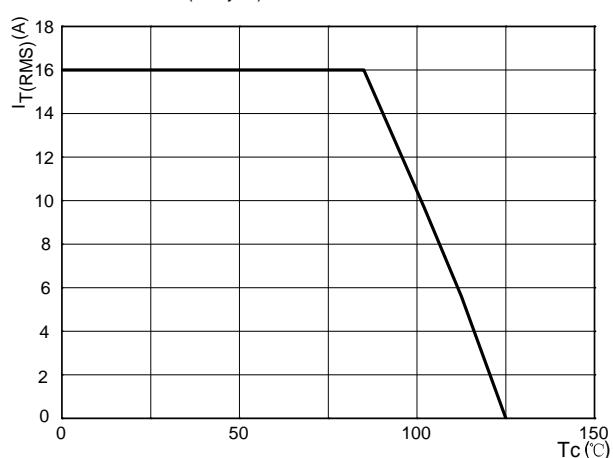


FIG.3: Surge peak on-state current versus number of cycles

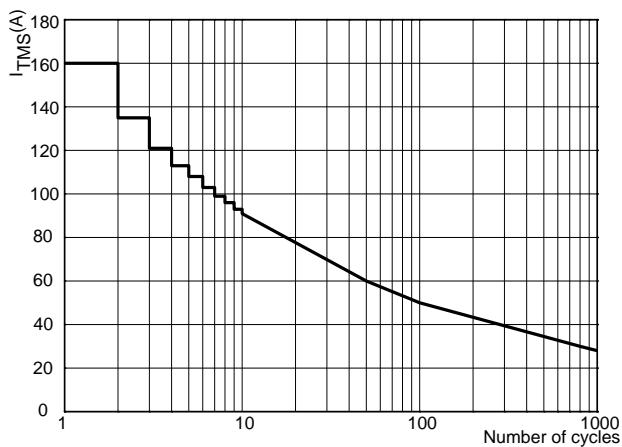


FIG.4: On-state characteristics (maximum values)

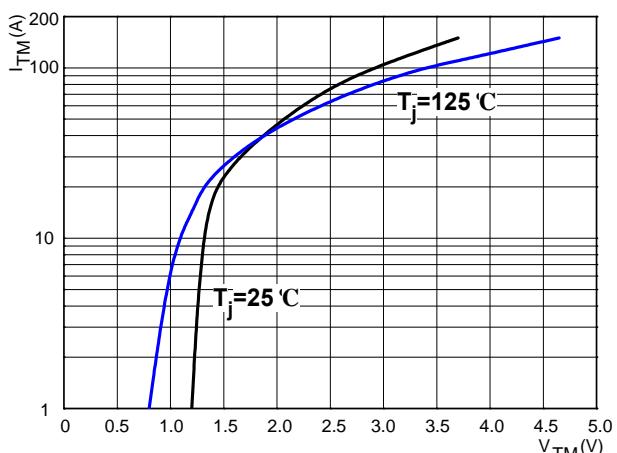


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10ms

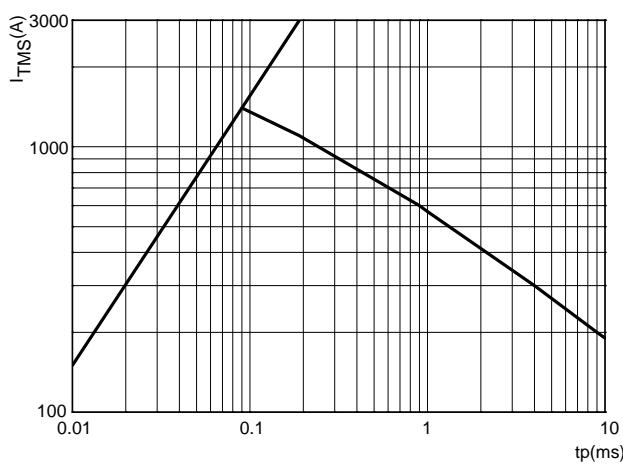
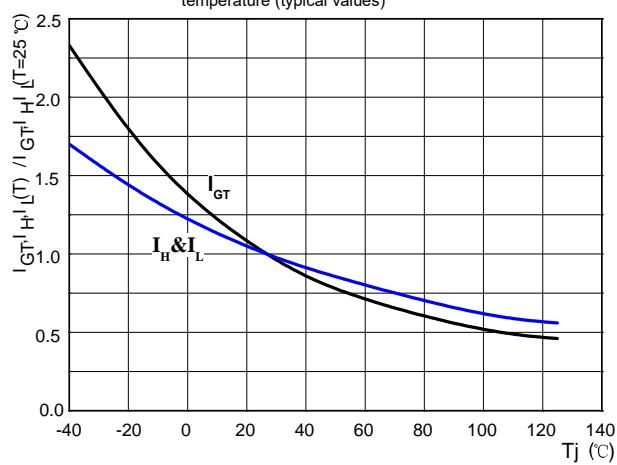
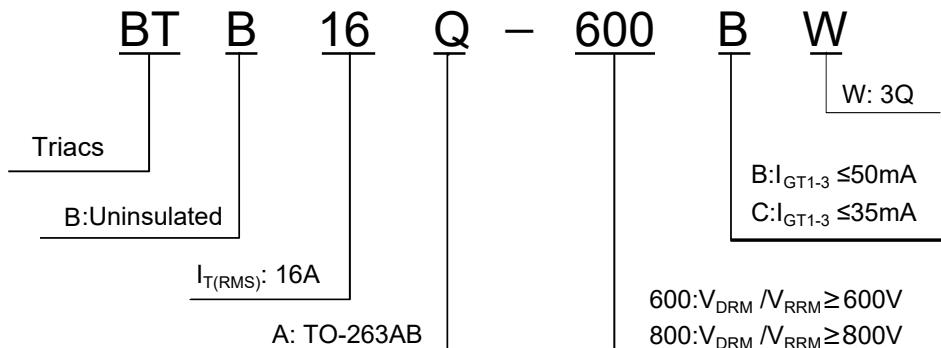


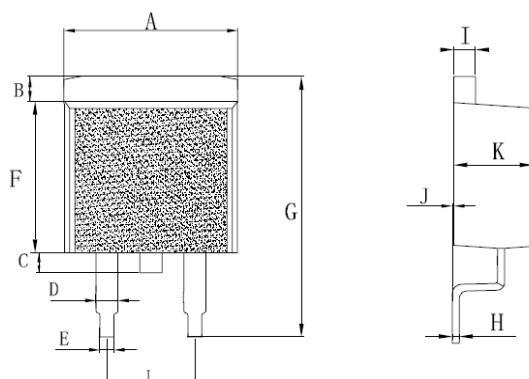
FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



## Ordering Information



## TO-263AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	9.7	10.4	0.381	0.409
B	1.31	1.62	0.051	0.063
C	0.65	1.22	0.025	0.048
D	1.15	1.36	0.045	0.053
E	0.62	0.95	0.024	0.037
F	8.75	9.32	0.344	0.366
G	14.75	15.8	0.580	0.622
H	0.32	0.48	0.012	0.018
I	1.18	1.36	0.046	0.053
J	0	0.15	0	0.005
K	4.38	4.86	0.172	0.191
L	4.85	5.23	0.190	0.205